BiVO4 photoanode with well controlled oxygen vacancy for enhanced photoelectrochemical properties

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BiVO4 photoanode for photoelectrochemical cell was synthesized by various methods. Through the 2-step electrodeposition method, thickness controlled BiVO4 film with porous structure could be prepared. For enhancing crystalline quality of BiVO4, V precursor was aged in MtOH solvent before reaction. Aged V precursor could make optimized BiVO4 crystal and enhanced film morphology. various condition of gas annealing was conducted to prepared BiVO4 samples for oxygen vacancy control. Modified BiVO4 samples with N2 gas and H2 mix gas showed 25% and 40% enhanced photocurrent density each. Not only photocurrent value but also onset potential was improved with cathodic shift. Enhanced photoelectrochemical properties of modified BiVO4 photoanode was analyzed through UV-vis. absorption and tauc plot, XPS, EIS, Mott-Schottky measurements. The modification method could be useful tool for oxide material based photoelectrochemical water splitting system.